Editorial

Advanced Nanostructured Semiconductor Materials: Morphology Controlled Synthesis and Application

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The increasing interest in morphology-control synthesized semiconductor nanomaterials and promising properties have led to the expanded application of semiconductor nanomaterials in nanoelectronics, field-effect transistor, light-emitting diodes, lasers, solar cells, chemical sensors and biosensors, nanopackaging, and catalysts. To date, various techniques such as chemical synthesis, self-assembly, and nanomanufacturing of bulk or layered wafers have been applied to morphology controlled synthesis novel semiconductor nanomaterials. We encourage the submissions of new methods and techniques in the morphology controlled synthesis and/or fabricated semiconductor nanomaterials and understanding the advanced optical, mechanical, electrical, or thermal properties of these as-prepared semiconductor nanomaterials. In this special issue, we invited researchers to contribute original articles as well as reviews that address the field of advanced nanostructured semiconductor materials. Today, we are very glad to see the sunset of issue with 5 research articles and one review paper published.

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